Supporting Information

Efficient white polymer light-emitting diodes from single polymer exciplex electroluminescence

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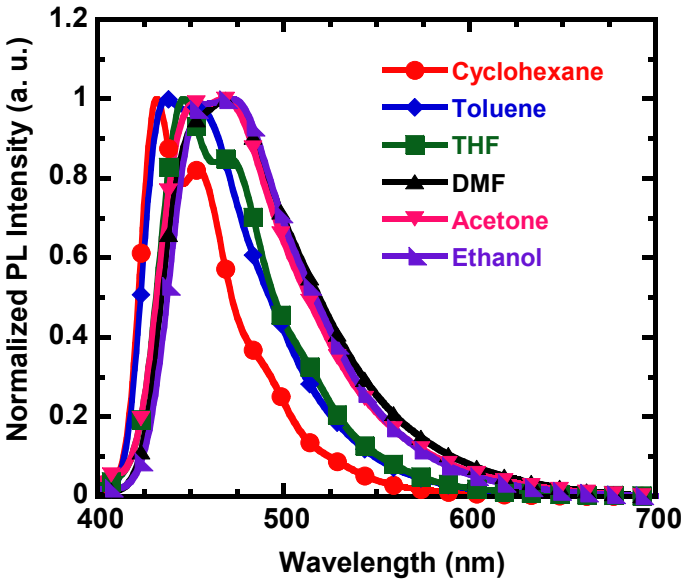

Figure S1. PL spectra of PFTS in various solvents with different polarity.

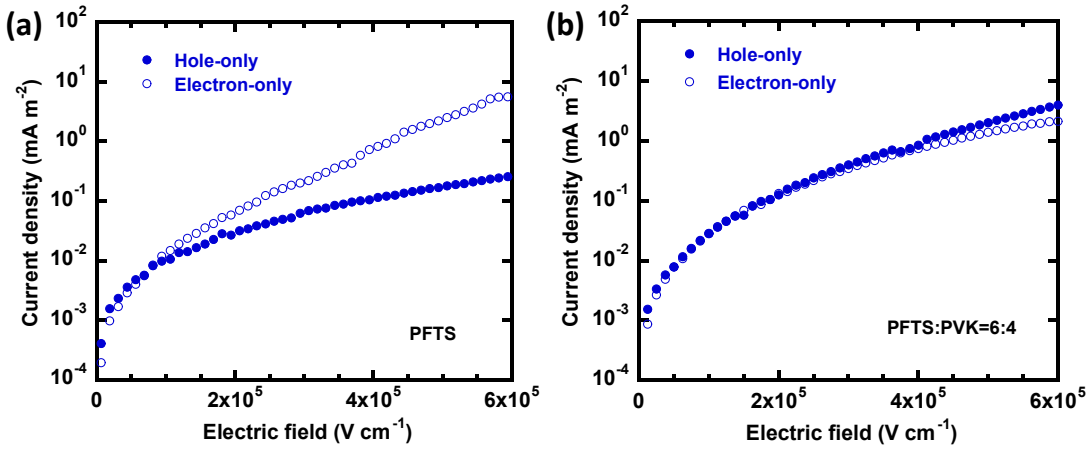

Figure S2. Hole only and electron only devices based on PFTS (a) and PFTS:PVK = 6:4. Structure for hole-only device: ITO/PEDOT:PSS(40 nm)/active layer (80 nm)/MoO_3 (10 nm)/Al (100 nm); electron-only device: ITO/ZnO (40 nm)/active layer (80 nm)/CsF(1.5 nm)/Al (100 nm).

Table S1. Hole and electron mobility of devices based on PFTS and PFTS:PVK.

Emissive layer	Hole mobility ($cm^2\ V^{-1}\ s^{-1}$)	Electron mobility ($cm^2\ V^{-1}\ s^{-1}$)
PFTS	2.13×10^{-8}	6.06×10^{-7}
PFTS:PVK = 6:4	2.44×10^{-7}	2.18×10^{-7}

* The mobilities are calculated based on space charge limited current method.

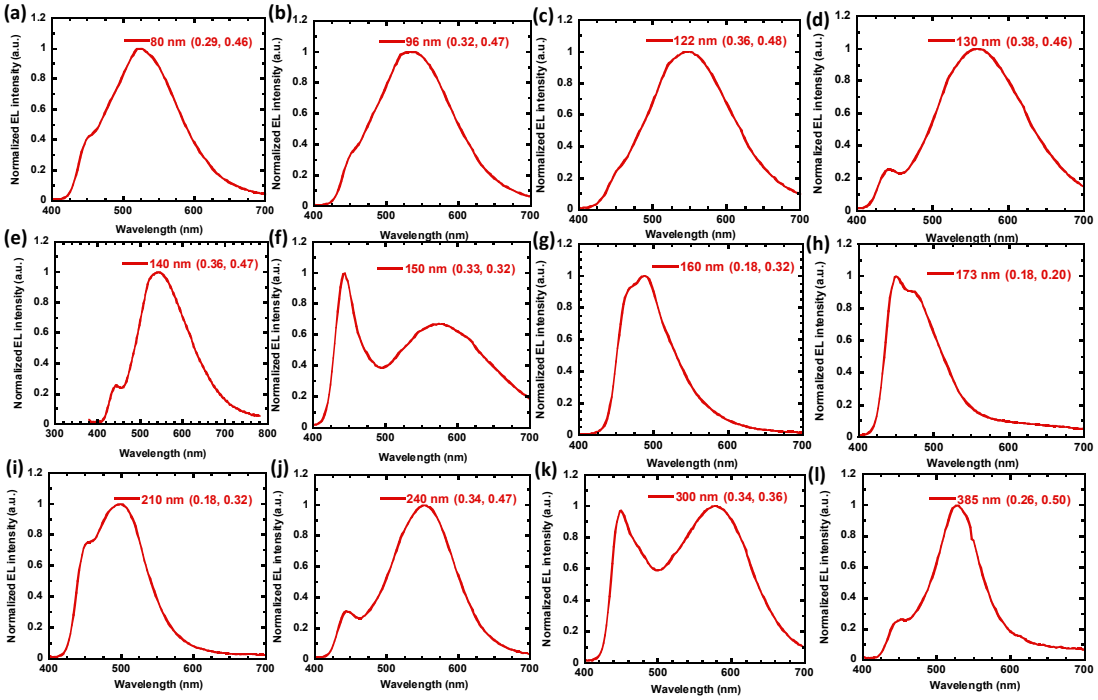

Figure S3. Electroluminescent spectra of devices with various thickness of the emissive layer. Device structure: ITO/PEDOT:PSS/PFTS:PVK/CSF/Al.

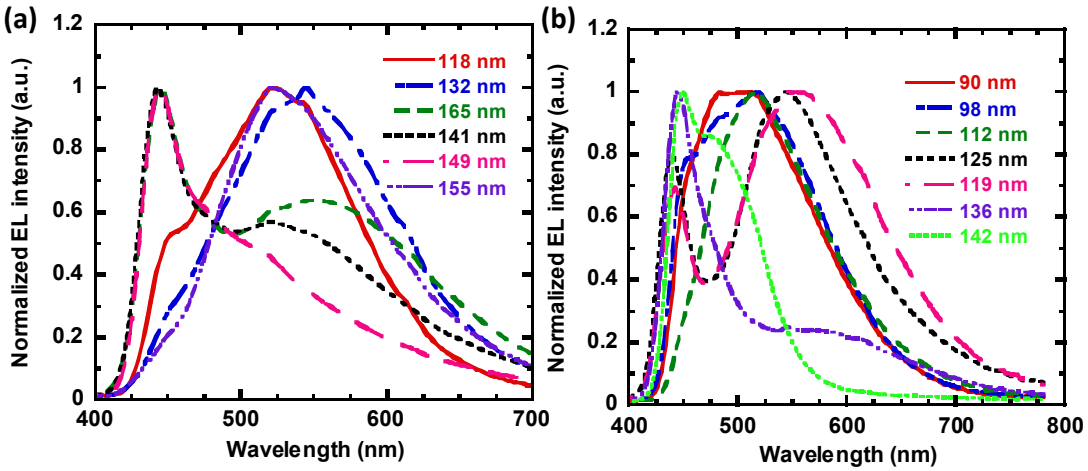

Figure S4. Electroluminescent spectra of devices with various thickness of the emissive layer, device structures: ITO/PEDOT:PSS/PFTS:PVK/CSF/Al (a); device structure: ITO/PEDOT:PSS/PVK/PFTS/CSF/Al (b).